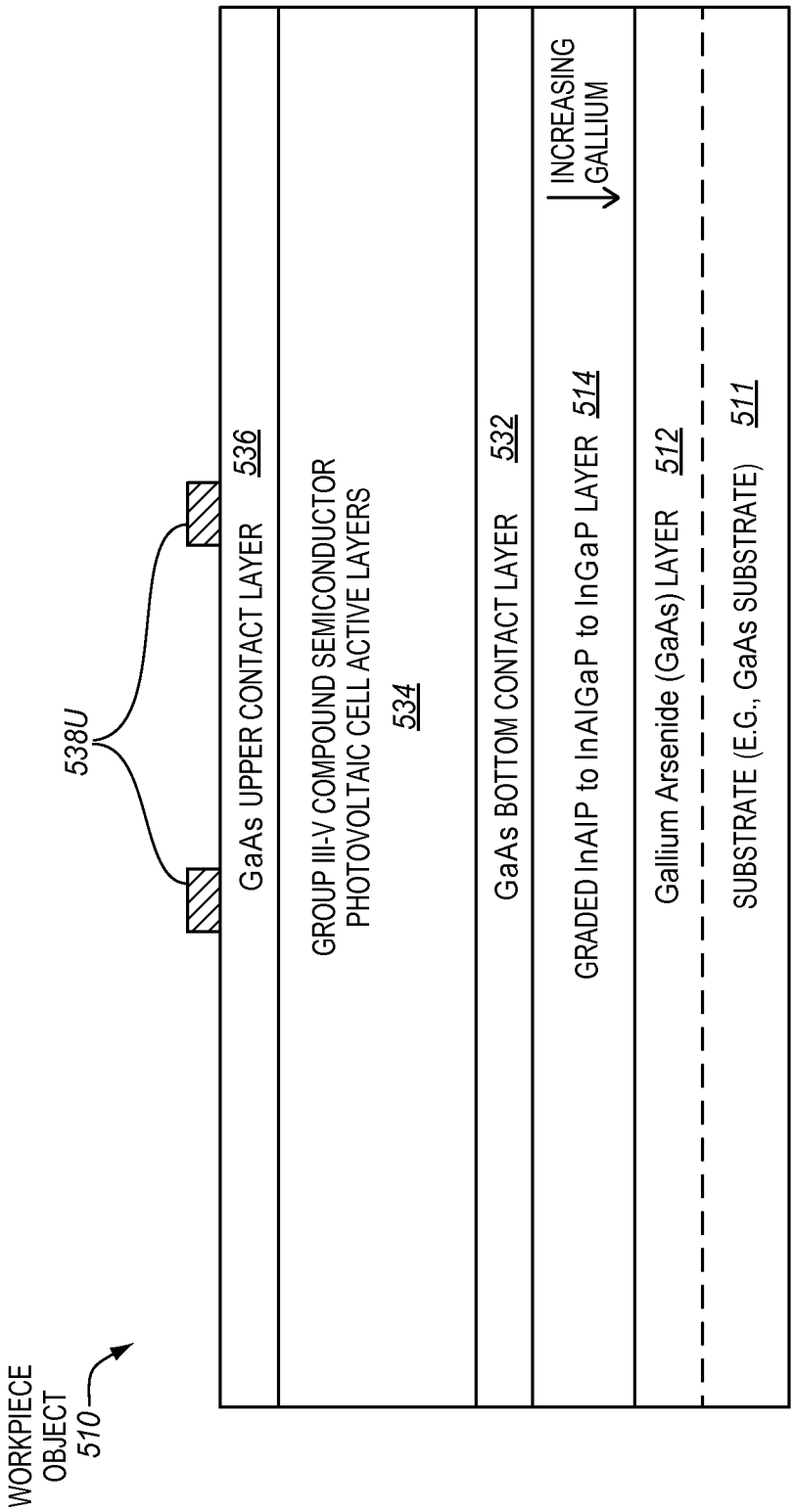
WORKPIECE OBJECT 510
538U
GaAs UPPER CONTACT LAYER 536
GROUP III-V COMPOUND SEMICONDUCTOR PHOTOVOLTAIC CELL ACTIVE LAYERS 534
GaAs BOTTOM CONTACT LAYER 532
GRADED InAlP to InAlGaP to InGaP LAYER 514
INCREASING GALLIUM
Gallium Arsenide (GaAs) LAYER 512
SUBSTRATE (E.G., GaAs SUBSTRATE) 511

FIG. 5